

L430-30T52 stem type LED

L430-30T52 is an InGaN LED mounted on TO-18 stem and hermetically sealed with flat glass can, being designed for sensing devices. On forward bias it emits a spectral band of radiation, which peaks at 405nm.

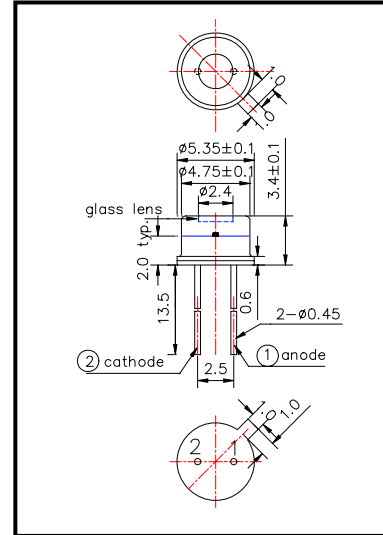
◆ Features

- 1) Wide viewing angle
- 2) High Reliability

◆ Specifications

- 1) Product Name LED Lamp
- 2) Type No. L430-30T52
- 3) Chip Spec.
 - (1) Material InGaN
 - (2) Peak Wavelength 430nm
- 4) Package
 - (1) Type TO-18 stem
 - (2) Lens $\Phi 2.4$ flat glass lens
 - (3) Cap Gold plated

◆ Outer dimension (Unit: mm)



◆ Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	PD	120	mW	Ta=25°C
Forward Current	IF	30	mA	Ta=25°C
Reverse Voltage	VR	5	V	Ta=25°C
Operating Temperature	TOPR	-30 ~ +85	°C	
Storage Temperature	TSTG	-30 ~ +100	°C	
Soldering Temperature	TSOL	260	°C	

‡Soldering condition: Soldering condition must be completed within 3 seconds at 260°C

◆ Electro-Optical Characteristics

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	IF=20mA		3.8	4.3	V
Reverse Current	IR	VR=5V			10	uA
Radiated Power	PO	IF=20mA		0.3		mW
Total Radiated Power	PO	IF=20mA		0.15		mW
Brightness	IV	IF=20mA		7		mcd
Radiant Intensity	IE	IF=20mA		0.15		mW/sr
Peak Wavelength	λP	IF=20mA	415	430	440	nm
Half Width	$\Delta\lambda$	IF=20mA		50		nm
Viewing Half Angle	$\theta 1/2$	IF=20mA		± 55		deg.

‡ Radiated Power is measured by AQ2730/AQ2741

‡ Total Radiated Power is measured by Photodyne #500

‡ Radiant Intensity is measured by Tektronix J-6512.